

PBSS5160U,115 Datasheet



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DiGi Electronics Part Number PBSS5160U,115-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PBSS5160U,115

Description TRANS PNP 60V 0.7A SOT323

Detailed Description Bipolar (BJT) Transistor PNP 60 V 700 mA 185MHz 4

15 mW Surface Mount SOT-323



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PBSS5160U,115	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	700 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
60 V	340mV @ 100mA, 1A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA	150 @ 500mA, 5V
Power - Max:	Frequency - Transition:
415 mW	185MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
SC-70, SOT-323	SOT-323
Base Product Number:	
PBSS5160	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0075	



PBSS5160U

60 V, 1 A PNP low VCEsat transistor

9 November 2023

Product data sheet

1. General description

PNP low V_{CEsat} transistor in a very small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4160U

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability $I_{\mbox{\scriptsize C}}$ and $I_{\mbox{\scriptsize CM}}$
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

3. Applications

- · High voltage DC-to-DC conversion
- High voltage MOSFET gate driving
- · High voltage motor control
- · High voltage power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-60	V
I _C	collector current		[1]	-	-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-2	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	255	340	mΩ

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



60 V, 1 A PNP low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	□ 3	
2	Е	emitter		C
3	С	collector		В
			1 2 SC-70 (SOT323)	E sym132

6. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
PBSS5160U	SC-70	plastic, surface-mounted package; 3 leads; 1.3 mm pitch; 2 mm x 1.25 mm x 0.95 mm body	SOT323				

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5160U	53%

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

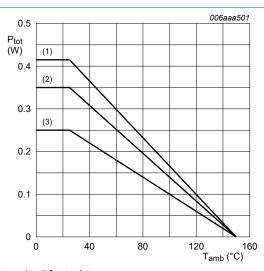
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-80	V
V _{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
Ic	collector current		[1]	-	-0.7	Α
			[2]	-	-0.86	Α
			[3]	-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-2	Α
I _B	base current			-	-300	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	250	mW
			[2]	-	350	mW
			[3]	-	415	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C

60 V, 1 A PNP low VCEsat transistor

Symbol	Parameter	Conditions	Min	Max	Unit
T_{stg}	storage temperature		-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	500	K/W
	junction to ambient	t	[2]	-	-	357	K/W
			[3]	-	-	301	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	150	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

60 V, 1 A PNP low VCEsat transistor

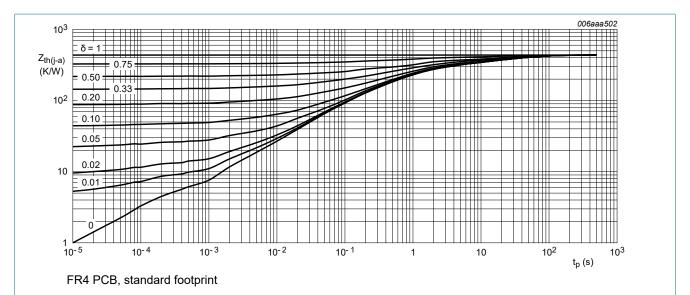


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

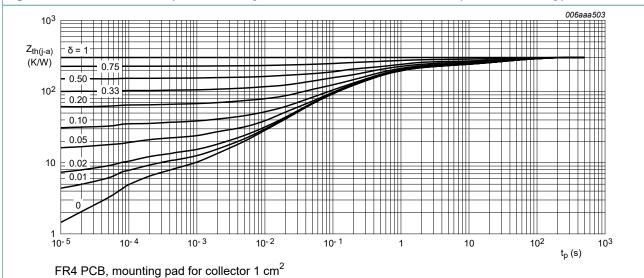


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

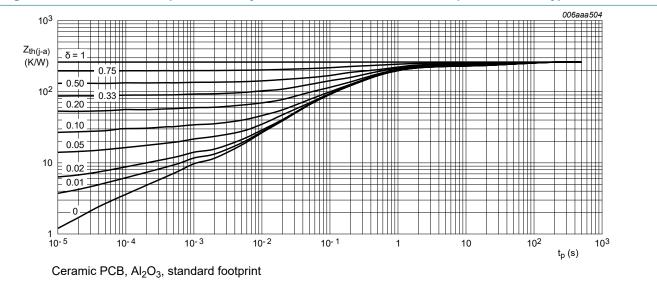


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -60 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -60 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = -60 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -1 mA; T_{amb} = 25 °C	200	350	-	
		V_{CE} = -5 V; I_{C} = -500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	150	250	-	
		V_{CE} = -5 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	160	-	
V _{CEsat}	/ _{CEsat} collector-emitter	I_C = -100 mA; I_B = -1 mA; T_{amb} = 25 °C	-	-110	-175	mV
	saturation voltage	I _C = -500 mA; I _B = -50 mA; T _{amb} = 25 °C	-	-135	-180	mV
		I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le$	-	-255	-340	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	255	340	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.95	-1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -5 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-0.82	-0.9	V
t _d	delay time	I _C = -0.5 A; I _{Bon} = -25 mA; I _{Boff} = 25 mA;	-	11	-	ns
t _r	rise time	T _{amb} = 25 °C	-	30	-	ns
t _{on}	turn-on time		-	41	-	ns
t _s	storage time		-	205	-	ns
t _f	fall time		-	55	-	ns
t _{off}	turn-off time		-	260	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	150	185	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	9	15	pF

60 V, 1 A PNP low VCEsat transistor

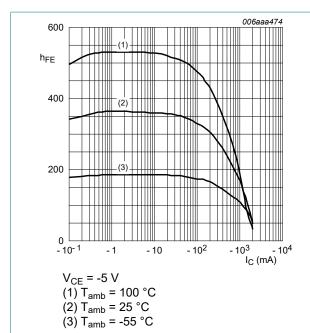


Fig. 5. DC current gain as a function of collector current; typical values

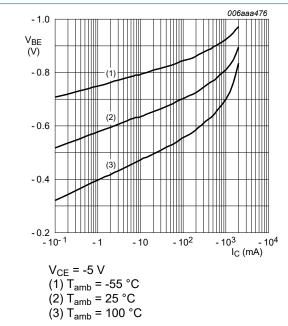


Fig. 7. Base-emitter voltage as a function of collector current; typical values

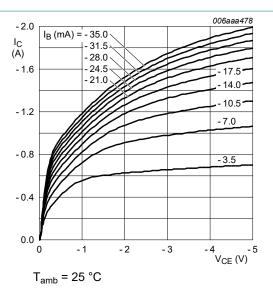
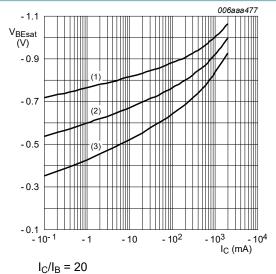


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



 $(1) T_{amb} = -55 °C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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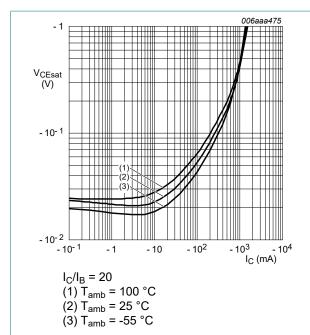


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

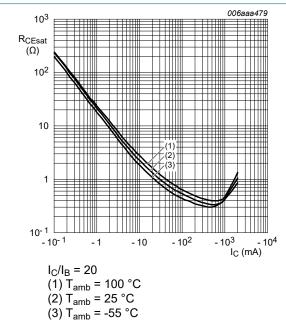


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

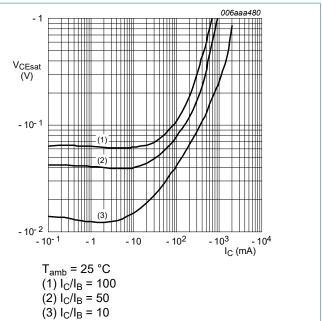
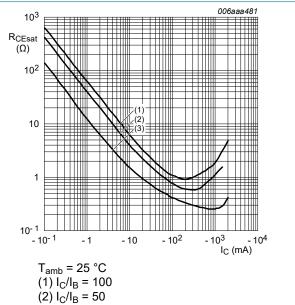


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

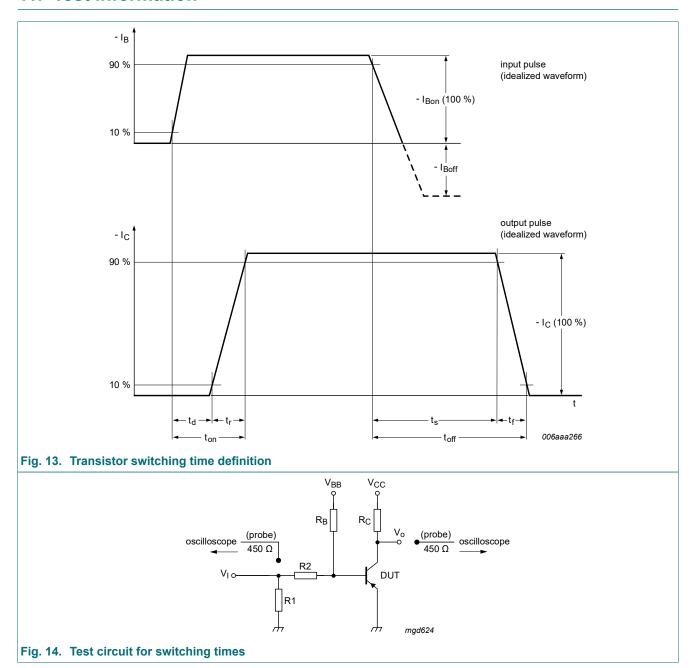


(3) $I_C/I_B = 10$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 1 A PNP low VCEsat transistor

11. Test information

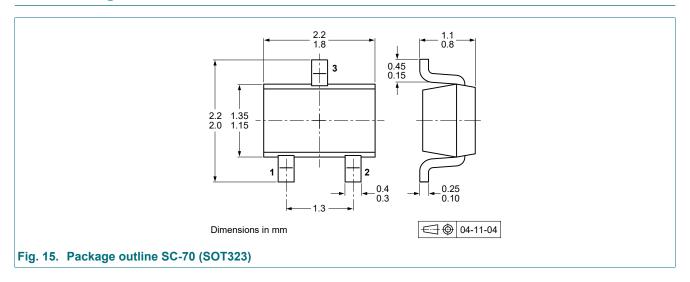


Quality information

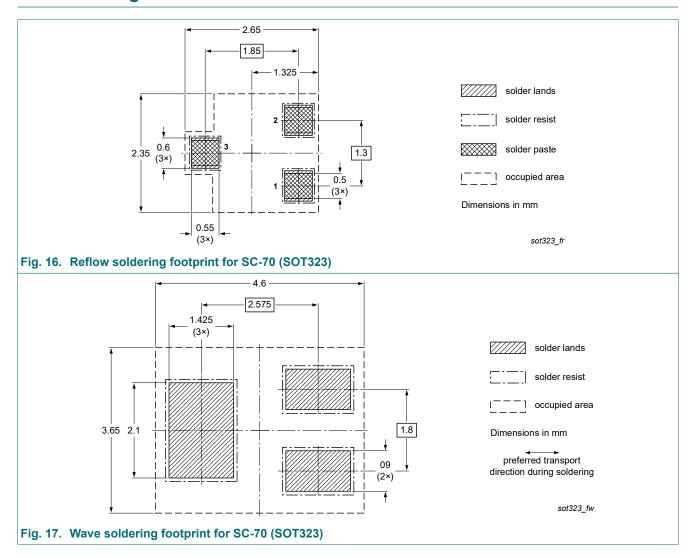
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 1 A PNP low VCEsat transistor

12. Package outline



13. Soldering



60 V, 1 A PNP low VCEsat transistor

14. Revision history

Table 8. Revision history

Table of Novicion motory						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5160U v.5	20231109	Product data sheet	-	PBSS5160U v.4		
Modifications:	Nexperia. • Legal texts ha	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Packing information removed. 				
PBSS5160U v.4	20081002	Product data sheet	-	PBSS5160U_3		
PBSS5160U_3	20050811	Product data sheet	-	PBSS5160U_2		
PBSS5160U_2	20040809	Objective data sheet	-	PBSS5160U_1		
PBSS5160U_1	20040503	Objective data sheet	-	-		

60 V, 1 A PNP low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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60 V, 1 A PNP low VCEsat transistor

Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	2
9. Thermal characteristics	
10. Characteristics	5
11. Test information	
12. Package outline	
13. Soldering	
14. Revision history	
15. Legal information	

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